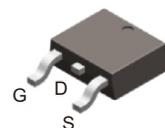


## ACMS100P04D-HF

**P-Channel**  
**RoHS Device**  
**Halogen Free**



### Features

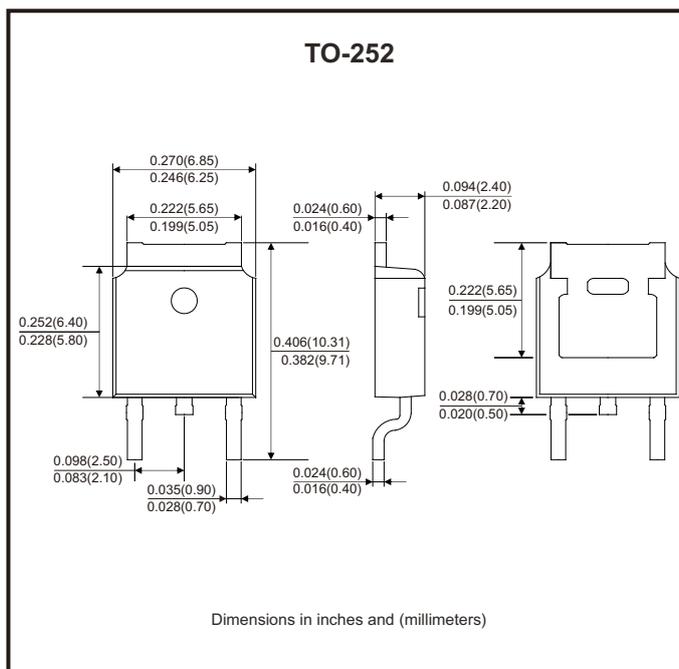
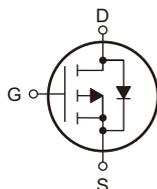
- Advanced trench technology.
- Super low on-resistance.
- Fast switching speed.
- AEC-Q101 Qualified.

### Mechanical data

- Case: TO-252, molded plastic.
- Terminals: Matte tin-plated leads, solderability-per MIL-STD-202, method 208.

### Circuit Diagram

- G : Gate
- S : Source
- D : Drain



### Maximum Ratings (at T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V <sub>DS</sub>	-40	V
Gate-source voltage	V <sub>GS</sub>	±20	V
Continuous drain current (T <sub>C</sub> =25°C)	I <sub>D</sub>	-100	A
Continuous drain current (T <sub>C</sub> =100°C)	I <sub>D</sub>	-63	
Continuous drain current (T <sub>A</sub> =25°C) (Note 1)	I <sub>D</sub>	-21	
Continuous drain current (T <sub>A</sub> =100°C) (Note 1)	I <sub>D</sub>	-13	
Pulsed drain current (tp=10μs, T <sub>C</sub> =25°C)	I <sub>DM</sub>	-400	A
Single pulse avalanche energy (Note 3)	E <sub>AS</sub>	340	mJ
Power dissipation (T <sub>C</sub> =25°C)	P <sub>D</sub>	114	W
Operating junction temperature range	T <sub>J</sub>	-55 to +150	°C
Storage temperature range	T <sub>STG</sub>	-55 to +150	°C

### Thermal Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Thermal resistance junction to case	R <sub>θJC</sub>		0.7	1.1	°C/W
Thermal resistance junction to air (Note 1)	R <sub>θJA</sub>		18	25	°C/W

## Electrical Characteristics (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-40			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -40V, V_{GS} = 0V$			-1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics</b>						
Static drain-source on-resistance (Note 2)	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -20A$		5	6.5	m $\Omega$
	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -10A$		6.5	9	m $\Omega$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.6	-2.5	V
Gate resistance	$R_G$	$V_{GS} = 0V, f = 1MHz$		2.9		$\Omega$
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = -25V, f = 100kHz$		6237		pF
Output capacitance	$C_{oss}$			472		
Reverse transfer capacitance	$C_{rss}$			426		
<b>Switching Characteristics</b>						
Turn-on delay time (Note 4)	$t_{d(on)}$	$V_{DD} = -20V, V_{GS} = -10V, R_G = 3\Omega, I_D = -20A$		16		ns
Turn-on rise time (Note 4)	$t_r$			17		
Turn-off delay time (Note 4)	$t_{d(off)}$			68		
Turn-off fall time (Note 4)	$t_f$			31		
Total gate charge	$Q_g$	$V_{DD} = -20V, V_{GS} = -10V, I_D = -20A$		125		nC
Gate to source charge	$Q_{gs}$			15.3		
Gate to drain (miller) charge	$Q_{gd}$			23.2		
<b>Source-Drain Diode Characteristics</b>						
Diode forward voltage (Note 2)	$V_{SD}$	$I_{SD} = -20A, V_{GS} = 0V$		-0.8	-1.2	V
Reverse recovery time	$t_{rr}$	$I_{SD} = -20A, V_{GS} = 0V, di/dt = 100A/\mu s$		61		ns
Reverse recovery charge	$Q_{rr}$			52		nC

- Notes: 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.  
 2. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .  
 3. The EAS data shows max. rating. The test condition is  $V_{DD} = -30V, V_{GS} = -10V, L = 0.5mH$ .  
 4. Guaranteed by design, not subject to production.

## Typical Rating and Characteristic Curves (ACMS100P04D-HF)

Fig.1 - Power Dissipation

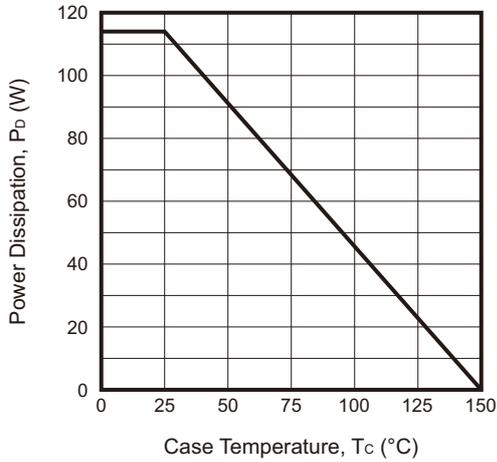


Fig.2 - Drain Current

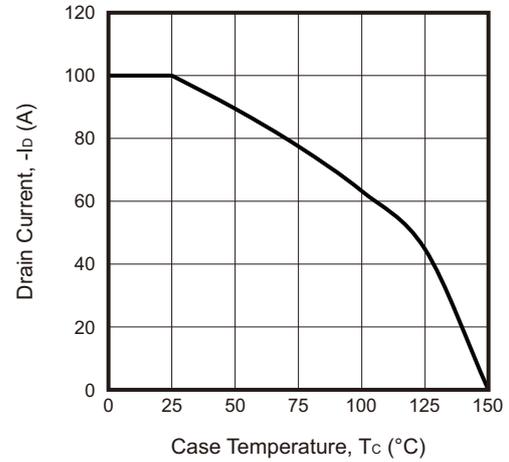


Fig.3 - Typical Output Characteristics

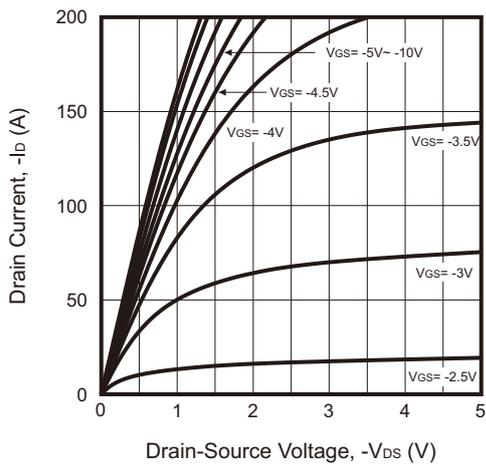


Fig.4 - On-Resistance vs. Drain Current and Gate Voltage

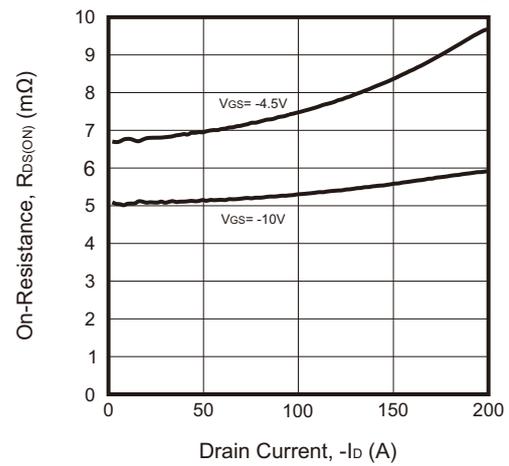


Fig.5 - On-Resistance vs. Gate-Source Voltage

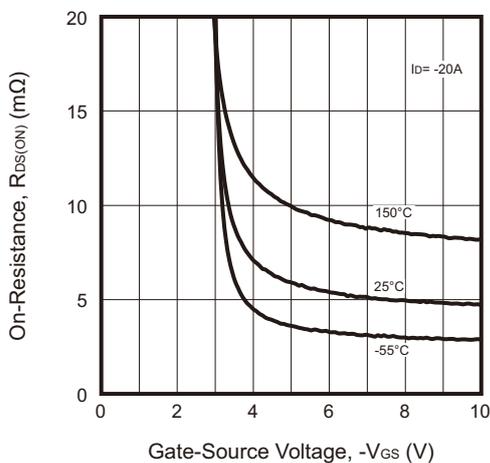
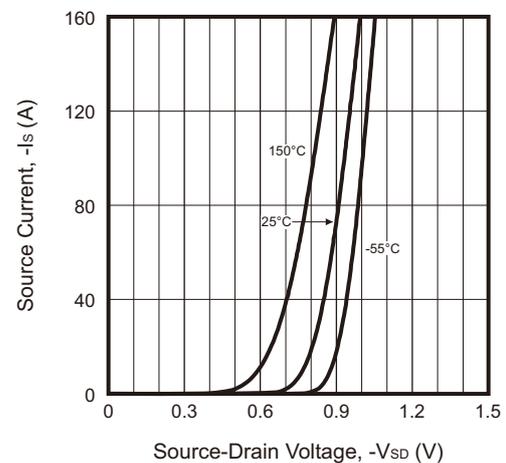


Fig.6 - Body-Diode Characteristics



## Typical Rating and Characteristic Curves (ACMS100P04D-HF)

Fig.7 - Normalized On-Resistance vs. Junction Temperature

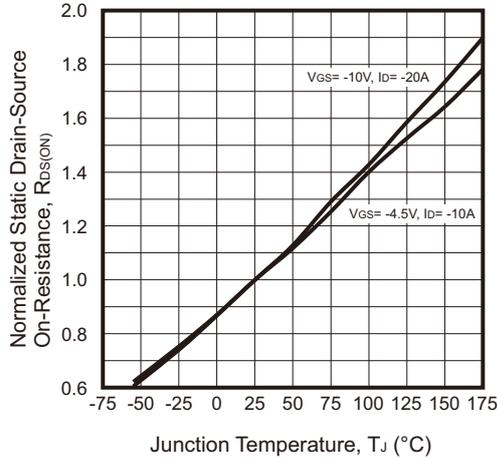


Fig.8 - Transfer Characteristics

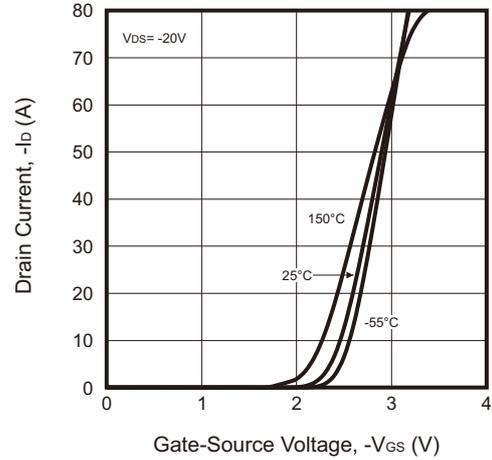


Fig.9 - Capacitance Characteristics

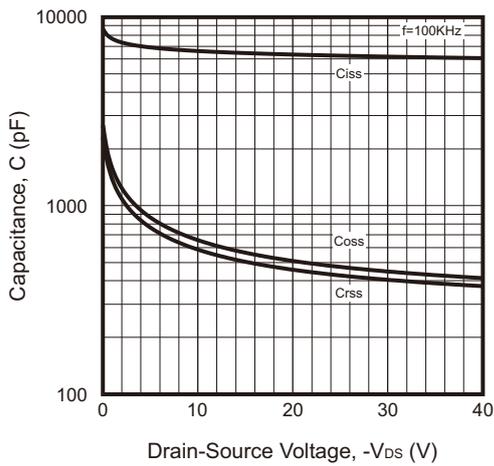


Fig.10 - Gate Charge Characteristics

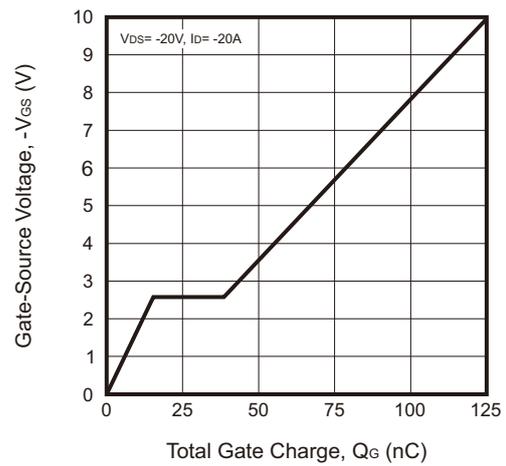


Fig.11 - Normalized Breakdown Voltage vs. Junction Temperature

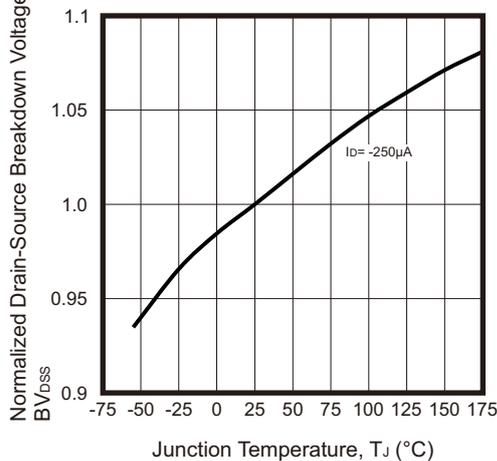
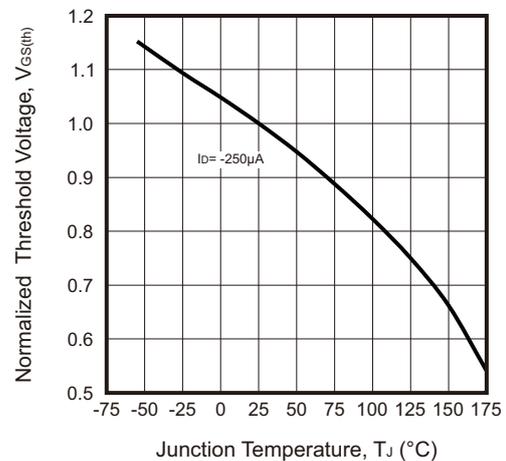
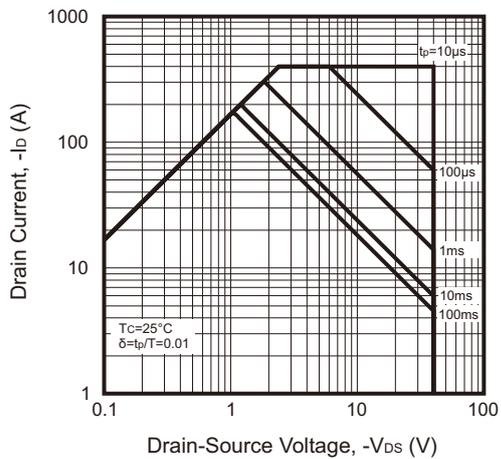


Fig.12 - Normalized V\_GS(th) vs. Junction Temperature

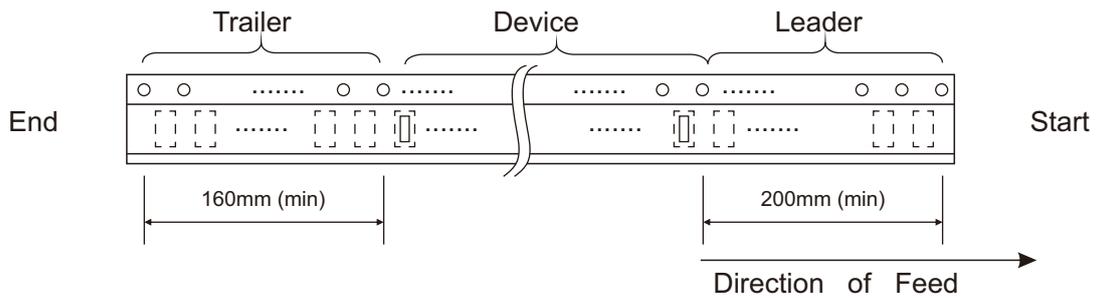
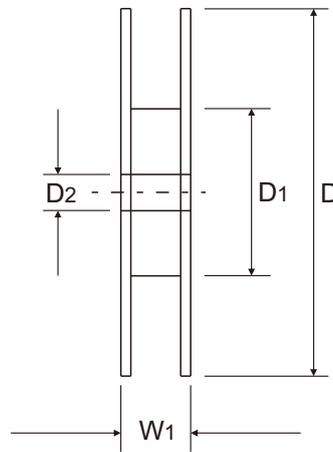
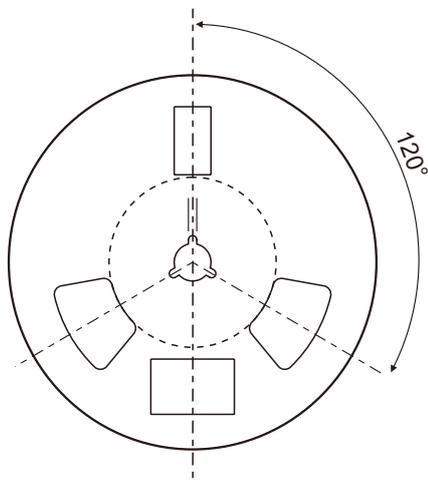
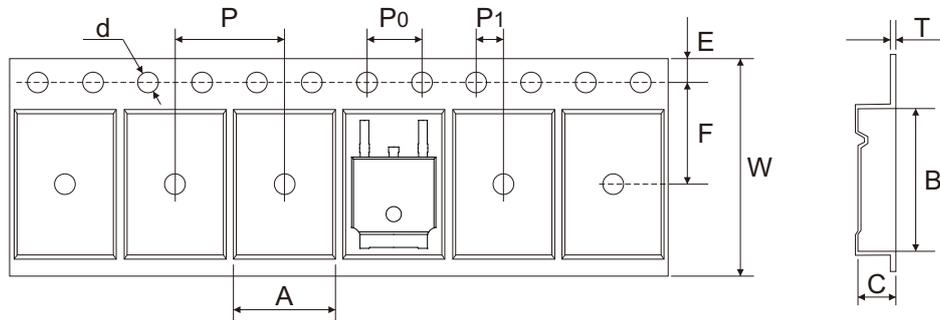


## Typical Rating and Characteristic Curves (ACMS100P04D-HF)

Fig.13 - Safe Operation Area



Reel Taping Specification

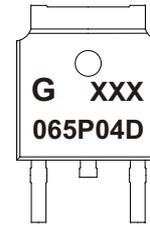


	SYMBOL	A	B	C	d	D	D1	D2
TO-252	(mm)	6.90 ± 0.10	10.50 ± 0.10	2.70 ± 0.10	1.50 + 0.25 - 0.00	330.00 ± 1.00	100.00 ± 1.00	13.00 ± 0.20
	(inch)	0.272 ± 0.004	0.413 ± 0.004	0.106 ± 0.004	0.059 + 0.010 - 0.000	12.992 ± 0.039	3.937 ± 0.039	0.512 ± 0.008

	SYMBOL	E	F	P	P0	P1	T	W	W1
TO-252	(mm)	1.75 ± 0.10	7.50 ± 0.10	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.30 ± 0.05	16.00 + 0.30 - 0.20	21.00 ± 0.30
	(inch)	0.069 ± 0.004	0.295 ± 0.004	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.012 ± 0.002	0.630 + 0.012 - 0.008	0.827 ± 0.012

## Marking Code

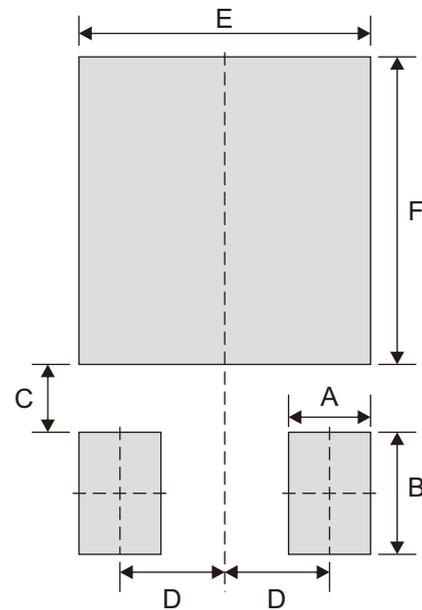
Part Number	Marking Code
ACMS100P04D-HF	065P04D



XXX = Control code

## Suggested P.C.B. PAD Layout

SIZE	TO-252	
	(mm)	(inch)
A	1.80	0.071
B	2.70	0.106
C	1.50	0.059
D	2.30	0.091
E	6.40	0.252
F	6.80	0.268



## Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
TO-252	2,500	13